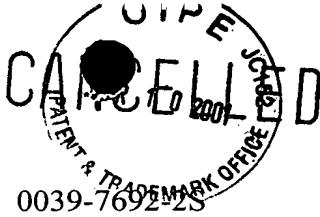


Atty. Docket #: 0039-7692-2S



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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

Akira GODA, et al. : GROUP ART UNIT: 2822

SERIAL NO: 09/556,777

FILED: APRIL 25, 2000 : EXAMINER: SOWARD, IDA M.

FOR: NONVOLATILE SEMICONDUCTOR
MEMORY DEVICE AND METHOD
FOR MANUFACTURING THE SAME

RECEIVED
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AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated December 10, 2001, please amend the above-identified application as follows:

IN THE SPECIFICATION

Please replace the paragraph beginning on page 5, line 17 with the following:¹

A1 A nonvolatile semiconductor memory device according to an aspect of the present invention comprises: a semiconductor substrate; and element isolation region formed in the semiconductor substrate, the element isolation region isolating a plurality of element regions in the semiconductor substrate; a first transistor formed in a peripheral circuit portion of the semiconductor substrate, the first transistor including source and drain diffusion layers

¹ A marked-up copy of the amended portion of the specification is attached hereto.